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## TABLE OF CONTENTS

Sr. No.	Title	Page No.
1	<b>Origin, Evolution and Termination of Micropipes in 4H-SiC Single Crystals</b> Xinyue Hou, Xiufei Hu, Xiufang Chen, Xianglong Yang, Xuejian Xie, Guanglei Zhong, Rongkun Wang, Xiangang Xu <b>Paper ID: PS001-20251113154516710</b>	1-13
2	<b>Optimization of Thermal Field for Large Scale SiC Growth with Resistance Heating Method</b> Peng Liu, Wancheng Yu, Ning Zhang, Xiyang Zhang, Wenhao Han, Xiufang Chen, Lihuan Wang, Xiaobo Hu, Xiangang Xu <b>Paper ID: PS002-20251007220233709</b>	14-17
3	<b>Characterization and analysis of 4H-SiC hydrophilic bonding based on plasma activation</b> Shuang Niu, Xiufei Hu, Dongyue Wu, Yong Yang, Muqing Zhang, Xiufang Chen, Rongkun Wang, Xuejian Xie, Huaying Ren, Guanglei Zhong, Xiangang Xu <b>Paper ID: PS003-20251023223636458</b>	18-21
4	<b>Study on Surface Damage of 12-Inch Silicon Carbide Wafers During Diamond Wire Cutting</b> Qingyu Li, Yong Yang, Wancheng Yu, Xiufang Chen, Xianglong Yang, Xuejian Xie, Rongkun Wang, Guanglei Zhong, Xiangang Xu <b>Paper ID: PS004-20251106201730387</b>	22-25
5	<b>The Influence of Doping on the Carrier Mobility of Semi-Insulating Silicon Carbide</b> Haoran Zhang, Xiufang Chen, Xuejian Xie, Li Sun, Desheng Wang, Xinglong Wang, Guanglei Zhong, Xianglong Yang, Xiaobo Hu, Dengfeng Zhang, Xiangang Xu <b>Paper ID: PS005-20251023092844082</b>	26-29
6	<b>Raman characterization and mapping of micro-area carrier concentration in 4H-SiC</b> Jun Du, Qizhi Li, Wei Liu, Hongyan Liu <b>Paper ID: PS006-20251007180958670</b>	30-33
7	<b>Enhancing Doping Concentration Uniformity and Batch Repeatability in 4H-SiC Homoepitaxy via Ammonia Doping</b> XIE Tianle, LIU Zhua, WAN Shengqianga, DENG Jiale, YANG Yu, LI Ping, LI Kuna, HU Fan, GONG Xiaoliang <b>Paper ID: PS007-20251106185548599</b>	34-37
8	<b>4H-SiC Homoepitaxy via Single-Source MTS Under Controlled Growth Temperatures</b> Hanyu Zhao, Yuyang Wang, Yicheng Pei, Moyu Wei, Yunkai Li, Jingyi Jiao, Han Kong, Chenlin Ai, Qing Katherine Mu, Guoguo Yan, Yingxi Niu, Xingfang Liu <b>Paper ID: PS008-20251105183310457</b>	38-42
9	<b>The Influence of Temperature on the Growth of SiC Thin Films via Solid Source</b> Yicheng Pei, Yuyang Wang, Hanyu Zhao, Moyu Wei, Yunkai Li, Jingyi Jiao, Wanshun Zhao, Lei Wang, Guoguo Yan, Xingfang Liu <b>Paper ID: PS009-20251007212021383</b>	43-46

---

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
10	<b>Effect of Growth Temperature on C-face 4H-SiC Homoepitaxy</b> Yuyang Wang, Hanyu Zhao, Yicheng Pei, Moyu Wei, Yunkai Li, Jingyi Jiao, Qing Katherine Mu, Guoguo Yan, Yingxi Niu, Xingfang Liu <b>Paper ID: PS010-20251105151145485</b>	47-51
11	<b>SiC Film Growth on Sapphire via Pyrolysis of Polycarbosilane</b> Hanyu Zhao, Yuyang Wang, Yicheng Pei, Moyu Wei, Yunkai Li, Jingyi Jiao, Han Kong, Chenlin Ai, Qing Katherine Mu, Guoguo Yan, Yingxi Niu, Xingfang Liu <b>Paper ID: PS011-20251105183328439</b>	52-56
12	<b>Synthesis of SiC Thin Films on Silicon Substrates via Pyrolysis of Solid Polycarbosilane Precursor</b> Yuyang Wang, Hanyu Zhao, Yicheng Pei, Moyu Wei, Yunkai Li, Jingyi Jiao, Qing Katherine Mu, Guoguo Yan, Yingxi Niu, Xingfang Liu <b>Paper ID: PS012-20251007225945993</b>	57-61
13	<b>Fabrication of 1200V800A Power module used of SiC trench MOSFETs</b> Shiyan Li, Fengbin Hao, Yang Yang, Yue Zhang, Xiaolei Yang, Runhua Huang, Song Bai <b>Paper ID: PS013-20251110135801881</b>	62-65
14	<b>A study on leakage current mutation in SiC junction barrier Schottky (JBS) diode</b> Qingling Li, Tao Zhu, Decai Liu, Jingmin Wu, Rui Jin <b>Paper ID: PS014-20251107135426400</b>	66-70
15	<b>1200V/13mΩ 4H-SiC MOSFET with Low Specific On-Resistance and High Avalanche Robustness</b> Rui Guo, Yue Zhang, Shiyan Li, Runhua Huang, Yong Yang, Song Bai, Longxin Shi <b>Paper ID: PS015-20251104162536194</b>	71-74
16	<b>Comparative Study of the Non-Self-Alignment and Self-Alignment Channel Processes for 4H-SiC MOSFET</b> Huan Ge, Naling Zhang, JiaLin Li, Tao Zhu, Zheyang Li, Zhiliang Yin, Wei Ma, Chao Leng, Rui Jin <b>Paper ID: PS016-20250814152808125</b>	75-78
17	<b>Short-Circuit Withstand Capability Improvement in Multi-Doped-Drift-Region SiC MOSFETs</b> Shijie Liu, Feng He, Yawei He, Handoko Linewih, Rui Jin <b>Paper ID: PS017-20251105184036857</b>	79-82
18	<b>Investigation on the Influence of Interface Traps Type, Energy Level and Location on I-V and C-V Characteristics in SiC MOSFET</b> Zhichao Cheng, Ling Sang, Feng He, Yawei He, Zheyang Li, Rui Jin <b>Paper ID: PS018-20251005143633420</b>	83-86
19	<b>A Novel 4H-SiC 3D Trench MOSFET with Punch-Through Protection and Gate Trench Bottom Implantation</b> Xinyue Lu, Jiupeng Wu, Na Ren, Kuang Sheng, Ji Cheng, Liming Wei, Jue Wang, Qing Yu <b>Paper ID: PS020-20251030155416977</b>	87-90

---

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
20	<b>Impact of Pre-Bias on the measured Threshold Voltage of SiC MOSFETs</b> Lingling Lai, Yingxin Cui, Fanpeng Zeng, and Jisheng Han <b>Paper ID: PS021-20251106092247716</b>	91-94
21	<b>Asymmetric Trench SiC MOSFET with Integrated MOS Channel Diode for Improved Reverse and Switching Performance</b> Zhaopeng Bai, Chengxi Ding, Yun-Duo Guo, Lin Gu, Hong-Ping Ma, and Qing-Chun Zhang <b>Paper ID: PS022-20251007193315551</b>	95-99
22	<b>Design and Simulation of the 19 kV N-Channel SiC IGBT: Buffer Stack Engineering for High Blocking Capability and Low Forward Voltage Drop</b> Yanjun Li, Hongyi Xu, Lingxu Kong, Xingyu Yan, Yuanying Li, Yefeng Wang, Ji Cheng, Liming Wei, Na Ren <b>Paper ID: PS023-20251008222241058</b>	100-103
23	<b>4H-SiC trench MOSFET with an ultra-low specific on-resistance of 1.87mΩ·cm<sup>2</sup></b> Yue Zhang, Song Bai, Shiyao Li, Runhua Huang, Yong Yang <b>Paper ID: PS024-20251104162404267</b>	104-107
24	<b>Simulation Design and Optimization of Ultra-High-Voltage 4H-SiC GTO with Implantation-Free JTE Terminations</b> Xingyu Yan, Na Ren, Yanjun Li, Lingxu Kong, Kuang Sheng <b>Paper ID: PS025-20251008235639098</b>	108-111
25	<b>Study on Carrier Concentration and Signal Enhancement of SiC MOSFET Based on SCM</b> Qin Hu, Fang Su, Di Wu, Qizhi Li, Yidan Chen, Jiamin Tian, Jun Du, Hongyan Liu and Kuang-Tse Ho <b>Paper ID: PS026-20251007181703483</b>	112-115
26	<b>The effect of different JFET ion implantation on the electrical performance and reliability of small-pitch 1200V SiC MOSFET devices</b> Ziwei Zhou, Yuanmiao Duan, Ying Dai, Yan Wang, Yuxi Wan, Gang Chen <b>Paper ID: PS027-20251104114938633</b>	116-118
27	<b>Characterization of 1350V-0.83mΩ·cm<sup>2</sup> SiC Semi-Super Junction SBD Based on Multi-step Trench</b> Yangyang Wu, Kuan Wang, Jun Yuan, Wei Chen, Zhijie Cheng, Zhikun Tao, Feng Guo, Qichao Ding, Minghua Zhu, Jin Rao, Guoqing Xin, Zhiqiang Wang <b>Paper ID: PS028-20251105150703930</b>	119-122
28	<b>Demonstration of a novel double shielding and current spreading SiC trench MOSFET with high robustness</b> Wei Chen, Jun Yuan, Kuan Wang, Yangyang Wu, Zhijie Cheng, Qichao Ding, Minghua Zhu, Jin Rao, Rong Zhang, Guoqing Xin, Zhiqiang Wang <b>Paper ID: PS029-20251106082054042</b>	123-126

---

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
29	<b>Design of a Novel LDMOS-SCR ESD Protection Device for SiC Power Integrated Circuits</b> Yaxin Wang, Yuan Yang, Yun Xia, Gang Chen, Xi Wang, Yuxi Wan, Daohua Zhang and Zhaonian Yang <b>Paper ID: PS030-20251112170216062</b>	127-130
30	<b>Methods for Testing and Online Monitoring of Key Parameters in Press-Pack IGBT Devices</b> Lu Yang, Rui Zhu, Ming quan Zeng, Yang Yu, Qing Guo <b>Paper ID: PS031-20251022120745396</b>	131-135
31	<b>Synergy of Silicon Deposition, Sacrificial Oxidation, and Nitrogen Annealing for Interface Quality Optimization in 4H- SiC MOS</b> Zhenyu Wang, Limin Yan, Hongping Ma <b>Paper ID: PS032-20251024183325115</b>	136-141
32	<b>Multi-physical simulation study on optimizing the temperature gradient in SiC single crystal PVT growth by regulating emissivity via roughness gradient on the outer wall of graphite crucible</b> Ming Zhou, Xunxi Zhang <b>Paper ID: PS033-20250814195457554</b>	142-146
33	<b>Automated detection method for defects in silicon carbide materials using deep neural networks</b> Wenjun Geng, Yongmeng Li, Haiping Shen <b>Paper ID: PS034-20251022195037984</b>	147-151
34	<b>Investigation of Hot Carrier Effects in 1200 V Planar-Gate SiC MOSFETs</b> Shilong Dai, Yidan Tang, Pengying Chang <b>Paper ID: PS035-20250930141339863</b>	152-155
35	<b>Spatiotemporal Electro-Thermal Dynamics and Design Strategies for Improved Short-Circuit Withstand in Asymmetric Trench SiC Power Devices</b> Xuanyu Jin, Yanjun Li, Manyi Ji, Yefeng Wang, Na Ren <b>Paper ID: PS036-20251106161208675</b>	156-159
36	<b>Failure Analysis of SiC Gate Turn-off Thyristor Under Repetitive Discharge Conditions</b> Xiaohong Li, Lishuai Han, Jiesen Li, Xia Luo, Xinghuan Chen, Shengzong He, Yijun Shi, Liang He, Yuan Chen <b>Paper ID: PS037-20251201170307750</b>	160-163
37	<b>Optimized Chip Layout for Press-Pack Power Modules Based on Thermal Distribution</b> Yangyi Shen, Mingquan Zeng, Ting Xu, Junze Li, Haoran Zhao, Qing Guo <b>Paper ID: PS038-20251020211439393</b>	164-169
38	<b>Design of an Online Junction Temperature Detection System for Power Devices Utilizing On-State Voltage</b> Kaicheng Luo, Mingquan Zeng, Li Liu, Qing Guo <b>Paper ID: PS039-20251009104141991</b>	170-174

---

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
39	<b>Thermal Oxidation Temperature-Dependent Carbon Cluster Formation at 4H-SiC/SiO<sub>2</sub> Interface Revealed by Electron Energy-Loss Spectroscopy</b> Jiamin Tian, Fang Su, Fangren Shen, Yawen Gui, Wei Liu, Qin Hu, Qizhi Li, Lei Yang, Changrun Cai, Wei Zeng, Hongyan Liu, Kuang-Tse Ho <b>Paper ID: PS040-20251007181109259</b>	175-177
40	<b>Investigation Of Avalanche Robustness On Different JFET Region Designs Of SiC MOSFET</b> Jianhua Shen, Yibo Zhang, Xiaoyan Tang, Qingwen Song, Hao Yuan, Chenyu Wang <b>Paper ID: PS041-20251201172420127</b>	178-182
41	<b>A BPNN-Based Solution for Thermomechanical Stress Analysis and Optimization of SiP Encapsulated Devices</b> Haiqi Wei, Jianna Zheng, Miao Cai, Ganggang Liu, Guolin Lin, Jianshu Lu, Daoguo Yang <b>Paper ID: PS042-20251103205353918</b>	183-187
42	<b>A 2.5D Hybrid Packaging Structure for Enhanced Dynamic Current Balancing in Multi-Chip SiC Power Module</b> Baolin Liu, Zihao Chen, Lejia Sun, Hao Yuan <b>Paper ID: PS043-20251105195039126</b>	188-191
43	<b>Effect of Processing Temperature on Reliability of Pressureless Sintered Silver</b> Xiaoqi Li, Chenshan Gao, Wenbo Wang <b>Paper ID: PS044-20251023155734237</b>	192-195
44	<b>Research on The Data Driving Optimization for a Bridgeless Boost PFC Circuit Using SiC Device</b> Chen Jiahui, Lin Weiming, Lin Songhui, Wang Yapeng, Li Fulong <b>Paper ID: PS045-20251007151413100</b>	196-200
45	<b>A Single-Stage Bridgeless Resonant LED Driver Using SiC Device And Its Hybrid Control Strategy</b> Li Fulong, Lin Weiming, Lin Songhui, Chen Jiahui, Wang Yapeng <b>Paper ID: PS046-20251007173406264</b>	201-205
46	<b>An AHBF LED Driver With Improved Hybrid Control Strategy</b> Wang Yapeng, Lin Weiming, Chen Hongxing, Chen Jiahui, Lin Songhui <b>Paper ID: PS047-20251008211749494</b>	206-210
47	<b>An Error Compensation Method for Junction Temperature Monitoring Based on the Inflection Point of Saturation Voltage Drop</b> Zhen Zhang, Baixun Zheng, Yifan Wang, Mingquan Zeng, Tao Wang, Qing Guo <b>Paper ID: PS048-20250930112757694</b>	211-214
48	<b>CMOS-Compatible Low-Temperature Au-Free Ohmic Contact Process for GaN</b> Jiajie Pan, Hanxiang Jia, Junlei He, Jie Ruan, Zongchao Liu, Panpan Wang, Bo Zhao, Sichao Li, Baohua Tan, Shuangzan Lu <b>Paper ID: PS049-20251021114832905</b>	215-218

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
49	<b>Anomalous Degradation and Recovery of p-GaN Gate HEMTs Under Repetitive Surge Voltage Stresses Within the Quantized Voltage Levels</b> Yuqi Liu, Jinggui Zhou, Binju Qiu, Enchuan Duan, Qi Zhou and Bo Zhang <b>Paper ID: PS050-20250929164405603</b>	219-222
50	<b>TCAD Investigation of Thick Bottom Oxide in GaN Trench-Gate MOSFETs for Electric Field Mitigation and Dynamic Performance Enhancement</b> Linkun Sun, Jing' ang Li, Maoqing Ling, Shengyang Gao, Kain Lu Low, Wen Liu <b>Paper ID: PS051-20251102105923422</b>	223-226
51	<b>Improved Electrical Properties of AlGaIn/GaN MIS-HEMT with PEALD-Grown Al<sub>2</sub>O<sub>3</sub> Gate Dielectric</b> Liu Wang, Peng Cui, Handoko Linewih, Siheng Chen, Xin Luo, Jiacheng Dai, Zhaojun Lin, Xiangang Xu, Jisheng Han <b>Paper ID: PS052-20250830190047357</b>	227-229
52	<b>Interface states characterization in GaN MISHEMTs with in-situ SiN gate dielectric using frequency-dependent conductance and deep level transient spectroscopy methods</b> Han Lin, Zirui Zhou, Kei May Lau, and Huaxing Jiang <b>Paper ID: PS053-20251107164826291</b>	230-232
53	<b>Enhancement-mode Operation in GaN Trigate Transistor with SiN<sub>x</sub>/AlN Dielectric Stack</b> Yu Li, Guohao Yu, Ang Li, Zhongming Zeng, and Baoshun Zhang <b>Paper ID: PS054-20251022183821815</b>	233-235
54	<b>Impact of Device Characteristics on Performance of Monolithic Integrated-GaN E/D Logic Inverters by Finite Element Simulation</b> Zelin Wu, Senyuan Xu, Tian Luo, Lekang Fan, Long Min, Zhuoran Luo, Yang Liu <b>Paper ID: PS055-20251124113139716</b>	236-239
55	<b>Process Optimization for Low-Leakage Quasi-Vertical GaN PiN Diode</b> Ying Liu, Wanyu Xu, Xiucheng Xu, Weiling Guo <b>Paper ID: PS056-20250904152257029</b>	240-243
56	<b>Influence of <math>\gamma</math>-Ray Irradiation on VTH Stability of P-GaN Gate HEMT</b> Chenyue Chu, Xuan Xie, Shibing Long, and Shu Yang <b>Paper ID: PS057-20251008231424286</b>	244-246
57	<b>Heavy-Ion-Induced Dynamic RON Degradation in GaN HEMTs: Mechanism and Suppression With AlGaIn Back Barrier</b> Minze Wang, Xuan Xie, Ziang Wang, Chenyue Chu, Guangwei Xu, Tianqi Wang, Shibing Long, and Shu Yang <b>Paper ID: PS058-20251023233607811</b>	247-250
58	<b>Effect of Gate-Injected Hole Drift on the Dynamic On-Resistance in Schottky-Type p-GaN Gate HEMT under Forward/Reverse Conduction</b> Peigeng Wang, Maojun Wang, Jin Wei, Zetao Fan, Jiaojiao Song, Yixuan Wang, Bo Shen <b>Paper ID: PS059-20251005190631211</b>	251-254

---

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
59	<b>Sidewall Damage Control in Quasi-Vertical GaN PiN Diodes on Silicon</b> Wanyu Xu, Zihan Ren, Haoran Gao, Weiling Guo, Yanxu Zhu <b>Paper ID: PS060-20251005203344698</b>	255-258
60	<b>A Monolithically Integrated GaN MIS-HEMT DFF Circuit for High Temperature and High Frequency Applications</b> Yihao Xu, Zhengxuan Li, Jie Jiao, Qiyuan Cui, Pingyu Cao, Kepeng Zhao, Yinchao Zhao, Miao Cui <b>Paper ID: PS061-20251029141514511</b>	259-262
61	<b>Low Cost AlN/GaN HEMTs on Sapphire for Low Voltage Terminal Application</b> Kun Yin, Qing Zhu, Jiejie Zhu, Xiaohua Ma <b>Paper ID: PS062-20251008012648728</b>	263-266
62	<b>Noise Performance of InAlN/GaN HEMTs on Sapphire Substrate for W-Band and D-Band Applications</b> Boyang Yi, Changxin Mi, Mengxiao Lian, Jiaheng He, Xuankun Wu, Shujie Xie, Zongyang Hu, Zhe Cheng, Xiaohong Yang, and Yun Zhang <b>Paper ID: PS063-20251106181500825</b>	267-270
63	<b>G-Band Pre-Matched GaN HEMTs with 2.6 dB Single-Stage Gain</b> C. Mi, B. Yi, Z. Hu, J. He, X. Wu, S. Xie, Z. Cheng, M. Lian, Q. Xie and Y. Zhang <b>Paper ID: PS064-20251106181551016</b>	271-274
64	<b>Effects of Different Passivation Structures on Millimeter-wave AlGaIn/GaN HEMTs</b> Xinyu Liu, Pengfei Wang, Xiangxin Cao, Minhan Mi <b>Paper ID: PS065-20251106213611240</b>	275-278
65	<b>Thermal Simulation of Structural Parameter in AlGaIn/GaN Fin-HEMT</b> Zihao Yang, Pengfei Wang, Minhan Mi, Jingyun Yao <b>Paper ID: PS066-20251106181636760</b>	279-281
66	<b>High-Efficiency Al<sub>2</sub>O<sub>3</sub>/AlN/GaN MIS-HEMTs for Low-Voltage RF Power Amplifiers</b> Shiyang Li, JieJie Zhu, Lingjie Qin, Bowen Zhang, Qing Zhu and Xiaohua Ma <b>Paper ID: PS067-20251106164259457</b>	282-284
67	<b>Ultralow Radio Frequency Loss for GaN on Sapphire</b> Kun Yin, Qing Zhu, Bowen Zhang, Jiejie Zhu, Xiaohua Ma <b>Paper ID: PS068-20251024142447403</b>	285-288
68	<b>Research on Performance Verification and RF Accelerated Life - Test of kW - level GaN Power Devices in P - band</b> Yin Jun , Zhang Xiaofan, Gao Yonghui, Wang Yi, Hu Yansheng, Wu jiafeng, Zheng Xuefeng, Wang Jinyan, Yu Ruoqi, Ni Tao, Zhai Yuwei, Xu Chunliang <b>Paper ID: PS069-20250814182145879</b>	289-299

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
69	<b>Investigation of angle effect on single-event leakage current degradation in Cascode GaN HEMTs</b> Zhinian Jin, Peipei Hu, Shiwei Zhao, Xiaoyu Yan, Danmei Lin, Pengfei Zhai, Yu Dong, Yuzhu Liu, Lijun Xu, Li Cai, Xuefeng Zheng and Jie Liu <b>Paper ID: PS070-20251025152713405</b>	300-304
70	<b>Impact Ionization Induced Anomalous Negative Bias Temperature Instability in Al<sub>2</sub>O<sub>3</sub>/AlN/GaN MIS-HEMTs</b> Shiyang Li, JieJie Zhu, Lingjie Qin, Huilin Li, Simei Huang, Qing Zhu and Xiaohua Ma <b>Paper ID: PS071-20251009145918997</b>	305-309
71	<b>GaN-Based High-Efficiency Two-Stage Converter with Buck and LLC for Aerospace Application</b> Qi Cao, Xinran Chen, Dejun Ba, Yuxin Niu, Yihe Wang, Xiaofeng Lyu <b>Paper ID: PS072-20251007230138472</b>	310-314
72	<b>Split-Path Bootstrap GaN MIS-HEMT Gate Driver for Fast Switching of Power Devices</b> Haoyu Wang, Yunsong Xu, Shenlei Ding, Jiangmin Gu, Kain Lu Low, Ang Li, Wen Liu <b>Paper ID: PS073-20251020185302794</b>	315-317
73	<b>A High Gain Operational Amplifier Circuit and Overcurrent Protection Module for GaN-based Power IC</b> Jixing Luo, Yan Zhang, Luqiao Yin, Aiyong Guo, Kailin Ren, and Jianhua Zhang <b>Paper ID: PS074-20251007185713820</b>	318-321
74	<b>Cryogenic GaN Monolithically ICs based on Hydrogen Treatment Technology</b> Ang Li, An Yang, Guohao Yu, Wen Liu, Zhongming Zeng, Baoshun Zhang <b>Paper ID: PS075-20251023135348116</b>	322-324
75	<b>Simualtion Study of a Novel ESD Protection Clamp with 3 HEMT for GaN Power Devices</b> Pengfei Zhang, Gaoqiang Deng, and Xiaorong Luo <b>Paper ID: PS076-20250929215057517</b>	325-327
76	<b>Linearity Analysis of Multi-loop Regulation Voltage Reference Based on GaN MIS-HEMTs</b> Ruiqi Gong, Hengzhi Qiu, Yunsong Xu, Jiangmin Gu, Ang Li, Wen Liu <b>Paper ID: PS077-20251029211356443</b>	328-331
77	<b>Experimental Study on Dynamic Resistance Characteristics of Ga<sub>2</sub>O<sub>3</sub> Schottky Barrier Diodes</b> Zijie Zhou, and Jiangbin Wan, and Hengyu Wang*, and Kuang Sheng <b>Paper ID: PS078-20251023153850108</b>	332-335
78	<b>Atomic Layer Etching of Ga<sub>2</sub>O<sub>3</sub> using SF<sub>6</sub> /BCl<sub>3</sub> Chemistry: Achieving Atomic-Scale Precision and Damage-Free Surface Preservation</b> Xiaoxiao Li, Luqiao Yin, Kailin Ren, Jianhua Zhang <b>Paper ID: PS079-20251009175108651</b>	336-339

---

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
79	<b>The Demonstration of Amperometric Ga<sub>2</sub>O<sub>3</sub> Two-step Trench Schottky Barrier Diode</b> Shaodong Xu, Jun Yuan, Ruoshi Peng, Mingzhe Li, Qiangmin Wei, Qichao Ding, Rong Zhang, Guoqing Xin, Zhiqiang Wang <b>Paper ID: PS080-20250928163946760</b>	340-343
80	<b>Simulation and Fabrication of an Edge Termination-Free Lateral <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> MESFET</b> Mingzhe Li, Jun Yuan, Shaodong Xu, Ruoshi Peng, Liyang Zhu, Qiangmin Wei, Qichao Ding, Rui Jin, Zheyang Li, Le Yu, Jiahui Wang, Rong Zhang, Guoqing Xin, Zhiqiang Wang <b>Paper ID: PS081-20250930144115576</b>	344-347
81	<b>Review of Mist-CVD Technology for Ga<sub>2</sub>O<sub>3</sub> Power and Optoelectronic Devices</b> Yang-Chao Liu, Man Luo, Xin Qi, Yi Shen, Qing-Chun Zhang, Hong-Ping Ma <b>Paper ID: PS082-20251008211855284</b>	348-351
82	<b>a-SnO<sub>x</sub>/ <math>\beta</math> -Ga<sub>2</sub>O<sub>3</sub> Junction Field-effect Phototransistor with High Responsivity and Fast Response Speed</b> Yuxia Xin, Yan Liu, Xiaolong Zhao, Hong Huang, Wentao Wu, Hong Huang and Shibing Long <b>Paper ID: PS083-20251115184256536</b>	352-355
83	<b>Nitrogen Ion Implantation at Trench Bottoms for Improved Reverse Blocking Performance in <math>\beta</math> -Ga<sub>2</sub>O<sub>3</sub> Schottky Barrier Diode</b> Gaofu Guo, Shige Dai, Yuhua Sun, Zheyuan Hu, Anjing Luo, Tiwei Chen, Chunhong Zeng, Zhucheng Li, Dengrui Zhao, Xiaodong Zhang, Zhongming Zeng, Baoshun Zhang and Xianqi Dai <b>Paper ID: PS084-20251023194956971</b>	356-359
84	<b>Recent Advances in Ohmic Contact with <math>\beta</math> -Ga<sub>2</sub>O<sub>3</sub>: A Review</b> Man Luo, Xin Qi, Yi Shen, Yang-Chao Liu, Qing-Chun Zhang, Hong-Ping Ma <b>Paper ID: PS085-20251009142526566</b>	360-363
85	<b>Current Aperture Vertical <math>\beta</math>-Ga<sub>2</sub> O<sub>3</sub> MOSFETs Featuring an N-ion Implanted Gate Shielding Layer</b> Ruoshi Peng, Mingzhe Li, Shaodong Xu, Jun Yuan, Qiangmin Wei, Qichao Ding, Rui Jin, Zheyang Li, Le Yu, Jiahui Wang, Rong Zhang, Guoqing Xin and Zhiqiang Wang <b>Paper ID: PS086-20251106172759501</b>	364-366
86	<b>High-Performance <math>\beta</math> -Ga<sub>2</sub>O<sub>3</sub> SBD and SiC MOSFET for High-Efficiency DC-DC Converter</b> Wei Guo, Qingyuan Hua, Yucheng Gao, Shenyang Mo, Qian Wang, Jian Luo <b>Paper ID: PS087-20250924085713829</b>	367-370
87	<b>Real-Time Junction Temperature Monitoring Using Lateral <math>\beta</math> -Ga<sub>2</sub>O<sub>3</sub> Schottky Barrier Diodes</b> Mingzhe Li, Jun Yuan, Shaodong Xu, Ruoshi Peng, Liyang Zhu, Qiangmin Wei, Qichao Ding, Rui Jin, Zheyang Li, Le Yu, Jiahui Wang, Rong Zhang, Guoqing Xin, Zhiqiang Wang <b>Paper ID: PS088-20251106161916208</b>	371-375

<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
88	<b>Research on <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Photoconductive Assisted Switch</b> Mingzhe Li, Jun Yuan, Ruoshi Peng, Shaodong Xu, Liyang Zhu, Qiangmin Wei, Qichao Ding, Rui Jin, Zheyang Li, Le Yu, Jiahui Wang, Rong Zhang, Guoqing Xin, Zhiqiang Wang <b>Paper ID: PS089-20250929183830268</b>	376-378
89	<b>TEB Pretreatment for Mg doped p-type h-BN</b> Dengrui Zhao, Li Zhang, Zhongming Zeng, Baoshun Zhang, Xiaodong Zhang and Xianqi Dai <b>Paper ID: PS090-20251008124733122</b>	379-382
90	<b>Electronic and optical properties modulation of heterostructures based on GaP and h-BN</b> Xiaotian Yang, Jun Zhang, Shiwei Ji, Jun J. Liou, Fang Wang, Yuhuai Liu <b>Paper ID: PS091-20250925131355720</b>	383-386
91	<b>Electronic properties of GaP/h-BN, GaP/h-BN/GaP, and h-BN/GaP/h-BN heterostructures</b> Cheng Li, Jun Zhang, Xiaotian Yang, Shiwei Ji, Yunhao Liu, Fang Wang, Yuhuai Liu <b>Paper ID: PS092-20251105101807267</b>	387-389
92	<b>The regulation of electronic properties in the h-BN/WTe<sub>2</sub> heterostructure by Al, P, and Si impurities</b> Jun Zhang, Cheng Li, Yunhao Liu, Xiaotian Yang, Shiwei Ji, Fang Wang, Jun J. Liou, Yuhuai Liu <b>Paper ID: PS093-20250928204536543</b>	390-393
93	<b>Optoelectronic Properties of HfSe<sub>2</sub>/h-BN Heterostructures Based on Different Stacking Methods</b> Yunhao Liu, Jun Zhang, Shiwei Ji, Xiaotian Yang, Fang Wang, Yuhuai Liu <b>Paper ID: PS094-20251029224443087</b>	394-396
94	<b>Embedded Microchannel DPC Ceramic Substrates for Enhanced LED Thermal Management</b> Jiuzhou Zhao, Yang Peng, Qing Wang <b>Paper ID: PS095-20251009092045327</b>	397-400
95	<b>Design of Gallium Nitride-based Pixel Driver Circuit for High Refresh-rate Micro-LED Display</b> Zijie Wang, Luqiao Yin, Aiying Guo, Kailin Ren and Jianhua Zhang <b>Paper ID: PS096-20251009115035133</b>	401-405
96	<b>Analysis of Factors Influencing the Performance of Quantum dots Color Conversion Layer in Micro - LED</b> Youxing Zhang, Xinyi Wang, Zhaoyu Chen, Luqiao Yin and Jianhua Zhang <b>Paper ID: PS097-20251019144451656</b>	406-409
97	<b>Wet Reflow of In Bumps with a SU-8 Solder Mask</b> Shuangjia Bai, Taifu Lang, Xin Lin, Shuaishuai Wang, Zhihua Wang, Chang Lin, Qun Yan and Jie Sun <b>Paper ID: PS098-20251031094746743</b>	410-414

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<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
98	<b>The Research on Optical Performance Testing of Laser lighting Products</b> Benliang Li, Liwen Gu <b>Paper ID: PS099-20251008234122684</b>	415-418
99	<b>Design and preparation of high-performance 760 nm VCSELs for TDLAS oxygen detection systems</b> Dan Cao, Ning Cui, Ao Qiu, Hongzhuo Wang, and Baolu Guan <b>Paper ID: PS100-20251006112118836</b>	419-422
100	<b>Characterization of Spatial Light Behavior in High-Brightness PiGF-Enabled Laser Lighting</b> Jiuzhou Zhao, Hongjin Zhang, Zikang Yu, Hao Cheng, and Yang Peng <b>Paper ID: PS101-20251107195728955</b>	423-426
101	<b>Enhanced Thermal Reflective PiGF@AlN Converter With Heat-conducting MgO Layer For Laser Lighting</b> Yunxi Chen, Zikang Yu, Jiuzhou Zhao, Hongjin Zhang, Yang Peng, Xin Liu, Li Liu <b>Paper ID: PS102-20251005144647679</b>	427-431
102	<b>Dual-Electrode Synergistic hole-array Structured UVA-LED</b> Hao Xu, Ying Liu, Rongjing Wang, Weiling Guo <b>Paper ID: PS103-20250923202304546</b>	432-435
103	<b>Simulation of Micro-LED Bonding and Reliability Based on Copper Pillar Bumps</b> Hao Fu, Zhu Yang, Xinhui Meng, Hong Fan, Xiuzhen Lu, Luqiao Yin and Jianhua Zhang <b>Paper ID: PS104-20250928100635526</b>	436-439
104	<b>Preparation of Blue GaN Micro-LED Array Based on Direct Laser Transfer and Thermocompression Bonding Process</b> Zhu Yang, Hao Fu, Xiaoxiao Ji, Min Wu, Guoxu Fang, Xiuzhen Lu, Luqiao Yin, Jianhua Zhang <b>Paper ID: PS105-20251021153642046</b>	440-443
105	<b>Optoelectronic characteristics of UVA micro-LEDs with different mesa sizes</b> Rongjing Wang, Ying Liu, Aoqi Fang, Hao Xu, Weiling Guo, Baolu Guan <b>Paper ID: PS106-20251107220342180</b>	444-447
106	<b>Performance improvement of AlGaN-based Deep Ultraviolet Laser Diode Performance with Multi-Step Quantum Barriers</b> Wenlan Ma, Xin Wang, Xinen Sang, Fang Wang, Jun. J Liou, Yuhuai Liu <b>Paper ID: PS107-20250929210750761</b>	448-451
107	<b>Enhanced Performance of N-Polar AlGaN-Based Deep Ultraviolet Light-Emitting Diodes by using Gradient Electron Blocking Layer Structure</b> Xien Sang, Haokai Jing, Fang Wang, Jun J. Liou, Yuhuai Liu <b>Paper ID: PS108-20250930115457088</b>	452-455
108	<b>Enhancing Deep-UV Laser Diode Performance through Collaborative Design of Quantum Barriers in P and N Sections</b> Xin Wang, Wenlan Ma, Xien Sanga Fang Wang, Yuhuai Liu <b>Paper ID: PS109-20250930133512223</b>	456-459

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<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
109	<b>Optimization of 254 nm Deep Ultraviolet Light-Emitting Diodes with Convex-Shaped Electron Blocking Layer</b> Aoxiang Zhang, Jiayi Yao, Fang Wang, Juin J. Liu and Yuhuai Liu <b>Paper ID: PS110-20251007183857496</b>	460-462
110	<b>Thermally Stable Quantum Dots Converted High-Power Light-Emitting Diodes</b> Shilong He, Zhongsheng Nie, Chong. Geng, Qing Li, Jay Guoxu Liu, and Shu Xu <b>Paper ID: PS111-20251007225414331</b>	463-467
111	<b>Compact Modelling on a-IGZO TFT Featuring Opto-electro-thermal Multiphysics Coupling</b> Guangfen Yao, Kaiyuan Zhao, Tianhao Zhu, Guanghua Chen, Jianhua Zhang, Jun Li, and Kailin Ren <b>Paper ID: PS112-20251005160628610</b>	468-472
112	<b>Optimization of AlGaIn-based deep ultraviolet light emitting diodes with trapezoidal hole blocking layer</b> Haokai Jing, Xien Sang, Xin Wang, Wenlan Ma, Fang Wang, Yuhuai Liu <b>Paper ID: PS113-20251023212254018</b>	473-476
113	<b>The Role of Panoramic Illuminance in Assessing the Illuminance Adequacy of Visual Elements</b> Meize Gu, Ling Xia <b>Paper ID: PS114-20251019215536599</b>	477-481
114	<b>Development and Validation of a Questionnaire on the Impact of Outdoor Light Pollution on Human Health</b> Jin Zhenghao, Lin Yandan <b>Paper ID: PS115-20250924164411104</b>	482-485
115	<b>A Study on Differences in Visual Function Between Black and East Asian Populations</b> Shupeng Li, Shanshan Zeng, Fang Hu, Jun Rong, Linhao Lu, Ya Guo, Jianqi Cai <b>Paper ID: PS116-20250916092335388</b>	486-490
116	<b>Comparative Analysis of Visual Function Variations Under Pulse Width Modulation (PWM) and Direct Current (DC) Dimming in Mobile Display</b> Yanlong Sun, Shanshan Zen, Hu Fang, Ya Guo, Shupeng Li, Jianqi Cai, Yi Chen <b>Paper ID: PS117-20250916092502503</b>	491-494
117	<b>Study on the Impact of Various Screen Color Temperatures on Visual Function in Esports</b> Linhao Lu, Shanshan Zeng, Shupeng Li, Fang Hu, Jun Rong, Ya Guo, Jianqi Cai, Zhi Lin <b>Paper ID: PS118-20250916172905702</b>	495-498
118	<b>Effects of Low Correlated Color Temperature Lighting on Relaxation</b> Boyuan Chen, Mingdao Zhang, Lin Guo, Jiawen Mao, Qi Dai <b>Paper ID: PS119-20251004145941678</b>	499-502
119	<b>HDR image reconstruction from single-exposure panorama for lighting quality assessment</b> Li Longliang, and Liu Xiaofeng ,Xia Ling <b>Paper ID: PS120-20251004205659148</b>	503-506

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<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
120	<b>Effects of Melanopic Illuminance on Pupil Diameter Under Constant Indirect Corneal Illuminance</b> Lin Guo, Yingying Huang, Jiawen Mao, Mingdao Zhang, Boyuan Chen, Zhixian Zhou, Lei Jia, Aihua Zheng, Xiaodong Guo, Biao Wang, Qi Dai <b>Paper ID: PS121-20251007153841128</b>	507-510
121	<b>Study on the Efficacy and Safety of Narrow-Spectrum Ultraviolet LED Combined with Red Light and Infrared Light LED Irradiation in Type 2 Diabetic Patients with Vitamin D Deficiency</b> Li Caige, Lan Wei, Zhang Xuefei, Zhang Lihui <b>Paper ID: PS122-20251024135342847</b>	511-514
122	<b>Importance of Doses and Dose-Response Modeling in Light Therapies: A Mini Review</b> Zhuowei Zhang and Jianfei Dong <b>Paper ID: PS123-20251104102902946</b>	515-518
123	<b>A single-stage step-down LED driver Combined with visible light communication modulation strategy</b> Lin Songhui, Lin Weiming, Chen Jiahui, Li Fulong, Wang Yapeng <b>Paper ID: PS124-20251101112221251</b>	519-523
124	<b>Automotive Interior Lighting: A study of Subjective Perception and Mood Statues for Napping and Waking Scenarios</b> Nuoyi Li, Wenqing Miao, Jun Song, Yandan Lin <b>Paper ID: PS125-20251013213232269</b>	524-527
125	<b>Finite Element Structural Analysis of Cu Bumps in Micro-LEDs with a Gold Passivation Layer</b> Junjian Liang, Hao Fu, Haojie Zhou, Luqiao Yin and Jianhua Zhang <b>Paper ID: PS126-20251031152504033</b>	528-531
126	<b>Investigation of Warpage Control and Solder Joint Reliability in Large Package Substrates with Integrated Partial Glass Cores</b> Yongpei Deng, Miao Cai, Qiqin Wei, Guolin Lin, Jianshu Lu, Yuan Li, Daoguo Yang <b>Paper ID: PS127-20251030205255404</b>	532-537
127	<b>Reliability Study of Au-Sn Bumps Based on Thermal Gradient Bonding for Micro-LED</b> Yanbin Zhu, Haojie Zhou, Boyan Zhao, Luqiao Yin Jianhua Zhang <b>Paper ID: PS128-20251007133552982</b>	538-541
128	<b>Thermal performance of glass interposer stacked packaging</b> Yongjin Zeng, Zhu Yang, Hao Fu, Luqiao Yin and Jianhua Zhang <b>Paper ID: PS129-20251109203834806</b>	542-545
129	<b>Current Sharing Design of Multi-Chip SiC Power Module Based on 3D-Laminated Cu-Clip Architecture</b> Yehui Meng, Haidong Yan, Yao Zhu, Miao Cai, Ji Cheng, Maosheng Zhang <b>Paper ID: PS130-20251203132713260</b>	546-549

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<b>Sr. No.</b>	<b>Title</b>	<b>Page No.</b>
130	<b>Analysis of Silver Sintering Processes Using Microfine Gas Flow-Assisted Pressure Sintering</b> Siyu Wu, Jianna Zheng, Miao Cai, Bofu Li, Shunfeng Han, Qiqin Wei, Daoguo Yang <b>Paper ID: PS131-20251203161926158</b>	550-554
131	<b>Monolithically Integrated GaN Hysteresis Comparator Based on Complementary Logic</b> Yutao Geng, Tao Chen, Yan Cheng, Yat Hon Ng, Ji Shu, and Kevin J. Chen <b>Paper ID: PS132-20251203170654886</b>	555-557
132	<b>Impact of Mg Doping Concentration on Hole Distribution and Transport in p-GaN/AlGaIn/GaN Heterostructure for Complementary Logic Integration</b> Yutao Geng, Yat Hon Ng, Tao Chen, Yan Cheng, and Kevin J. Chen <b>Paper ID: PS133-20251203170534566</b>	558-560
133	<b>Optical Study of Dam Absorbing Devices Based on Micro LED</b> Wei Wei, Chen Lei, Zou Jun, SONG Jinde, Le Gang, Chen Zhizhong <b>Paper ID: PS134-20251203205031959</b>	561-566
134	<b>Research on Replacing Fluorescent Tube with UV LED Light Source Based on Total Reflection Little Angle UV Packaging Technology</b> Wei Wei, Zou Jun, Song Jinde, Xiong Jingkan , Zhang Guoyi <b>Paper ID: PS135-20251203205059692</b>	567-570